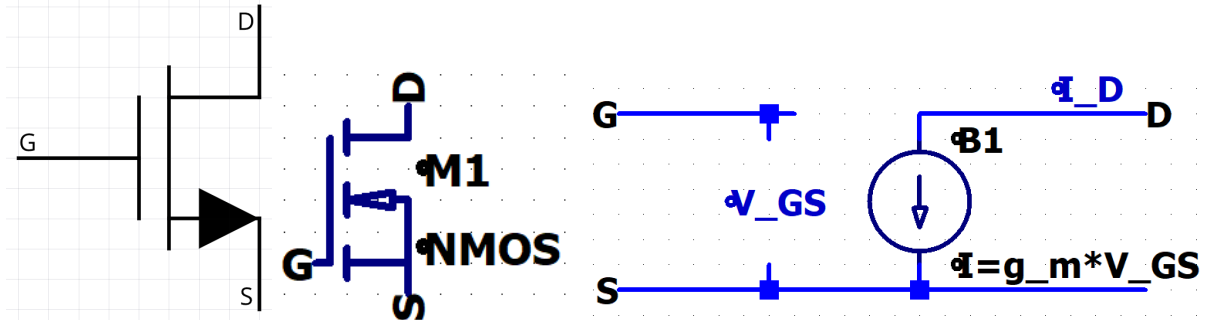


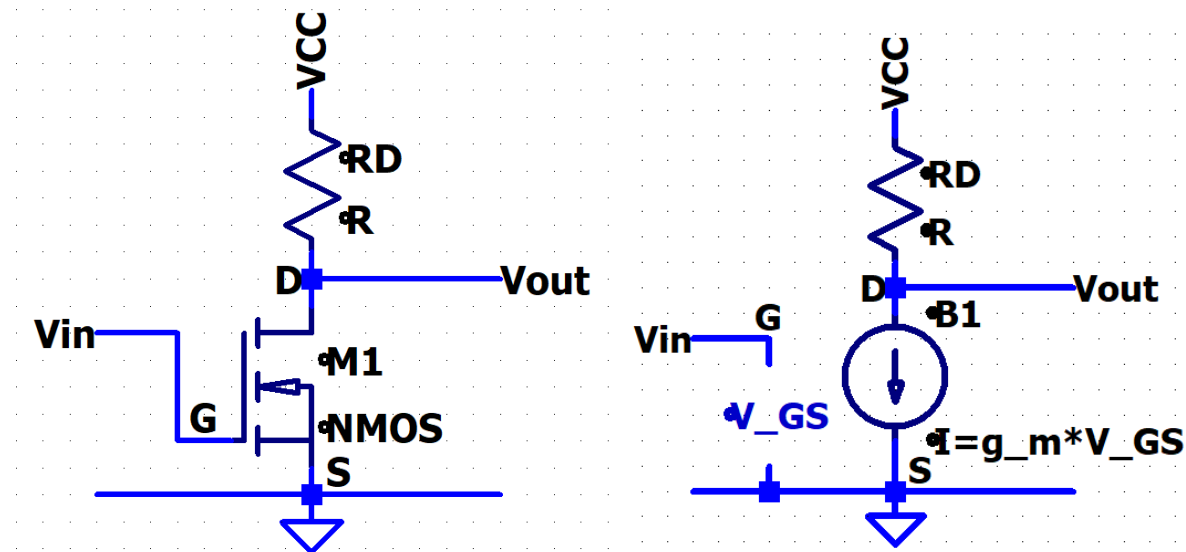
1. FET amplifier circuits:

The present problem concerns common-source, common-drain, and common-gate amplifier circuits. Assume that the amplifiers do not have a gate-biasing-resistor network.

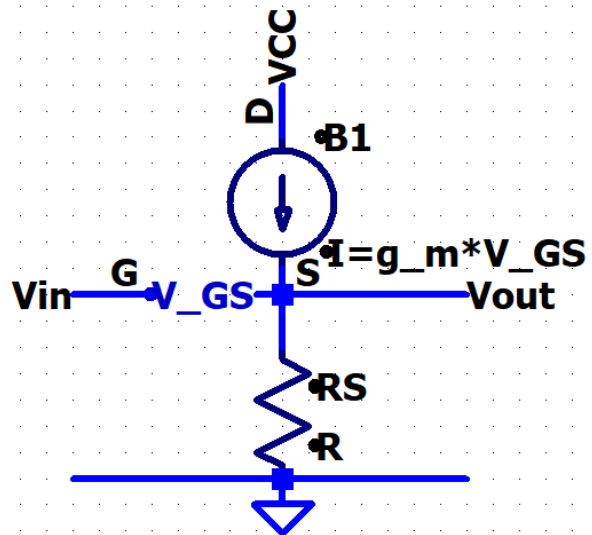
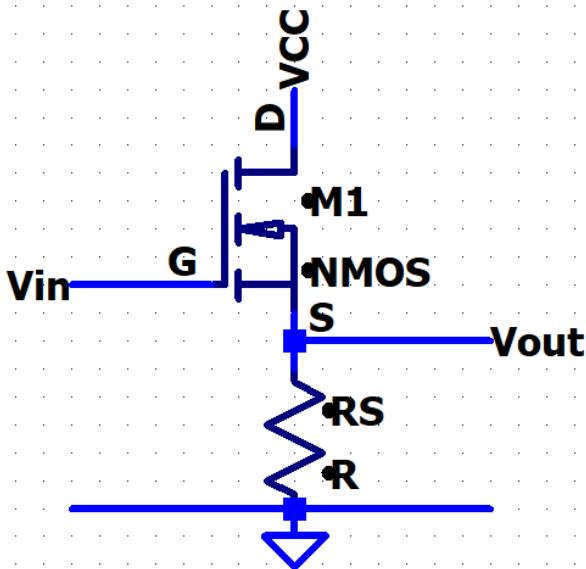
- a. (a) Draw the FET circuit symbol of an n-channel FET and the corresponding AC small-signal equivalent circuit.



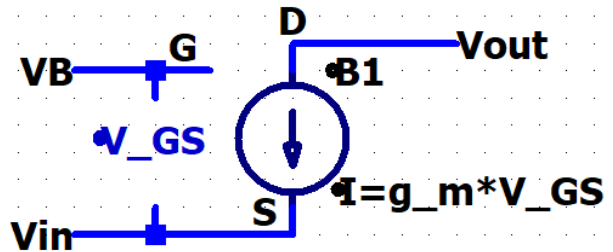
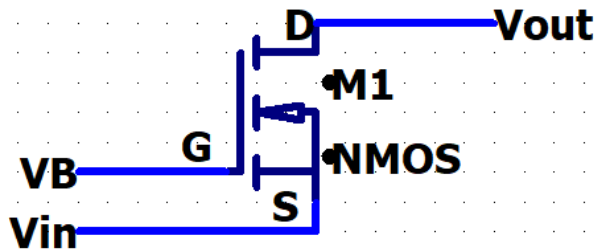
- b. (b) Draw a basic common-source (common-S) amplifier circuit and include a drain resistance R_D (but no other resistance). Draw the AC small-signal equivalent circuit of the amplifier (mark the G, S, and D terminals). Derive a symbolic expression for z_{in} (input impedance), z_{out} (output impedance), A_{VOC} (open-circuit voltage amplification), and A_{ISC} (short-circuit current amplification).



- c. (c) Draw a basic common-drain (common-D) amplifier circuit and include a source resistance R_S (but no other resistance). Follow the same instructions as for the previous question.



- d. (d) Draw a basic common-gate (common-G) amplifier circuit and do not include any resistor. Follow the same instructions as for the previous question.



- e. (e) Make a table having three columns listing the three basic transistor configurations (common-source, common-drain, and common-gate configuration) and four rows listing the amplifier parameters (z_{in} , z_{out} , $AVOC$, and $AISC$).

Amp [with additions]]	Common S	Common D	Common G
Z_{in}	Infinite $[R1 R2]$	Infinite $[R1 R2]$	$1/g_m$
Z_{out}	R_D	$R_S [R_S/(g_m R_S + 1)]$	$0 [g_m R_S r_0]$
$AVOC$	$-g_m R_D$ $[-g_m R_D(1 + g_m R_S)]$	$g_m R_S / (1 + g_m R_S)$	Infinite $[g_m R_L]$
$AISC$	Infinite $[g_m(R1 R2)]$	Infinite $[g_m(R1 R2)]$	1
notes	High $AISC$	$AVOC \sim 1$, $S=G$, source follower	Less common, low noise, easy z match

f. (f) Which of the three circuits has the lowest output impedance? Is this desirable?
Common D, this is desirable for a voltage source, making a good voltage follower.

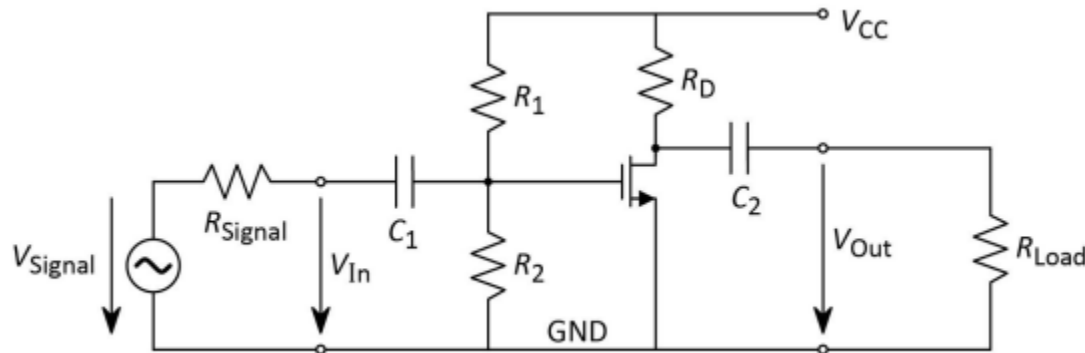
g. (g) Which of the three circuits has the lowest input impedance? Is this desirable?
Common G, this is desirable for a current source, making a good current follower.

h. (h) Which of the three circuits has a voltage amplification (AVOC) of about 1.0?
Common D,

i. (i) Which of the three circuits are the most useful ones?
They all have their uses, but common S is probably the most commonly used one

2. FET amplifier circuit and Miller capacitance:

The present problem concerns an FET amplifier circuit and its frequency response. The circuit diagram is shown in the figure below. The FET has a k -value of $k = 20 \text{ mA/V}^2$ and a threshold voltage of $V_{th} = 1 \text{ V}$. The FET gate-bias network consists of two resistors with $R_1 = 80 \text{ k}\Omega$ and $R_2 = 20 \text{ k}\Omega$. The AC signal source has an AC voltage amplitude of V_{Signal} and an internal resistance of $R_{Signal} = 5 \text{ k}\Omega$. The load resistance is $R_{Load} = 1 \text{ k}\Omega$. The DC power supply voltage is $V_{CC} = 10 \text{ V}$. Assume that the capacitors C_1 and C_2 are sufficiently large to let pass all AC signals (yet block DC signals).



- a. (a) Which one of the three basic amplifier configurations does the present amplifier have? Determine the Q-point of the amplifier circuit by calculating the drain current I_D .

Common S,

$$V_{GS} = V_{CC} \frac{R_2}{R_1 + R_2} = 10\text{V} \cdot \frac{20\text{k}\Omega}{80\text{k}\Omega + 20\text{k}\Omega} = 2\text{V}$$

$$I_D = \frac{1}{2} k (V_{GS} - V_{TH})^2 = \frac{1}{2} 20\text{mA/V}^2 (2\text{V} - 1\text{V})^2 = 10\text{mA}$$

- b. (b) Choose R_D so that the Q-point is in the middle of the load line, that is, at $V_{DS} = 5 \text{ V}$.

$$V_{DS} = V_{CC} - V_{RD}$$

$$5\text{V} = 10\text{V} - V_{RD}$$

$$V_{RD} = 5\text{V}$$

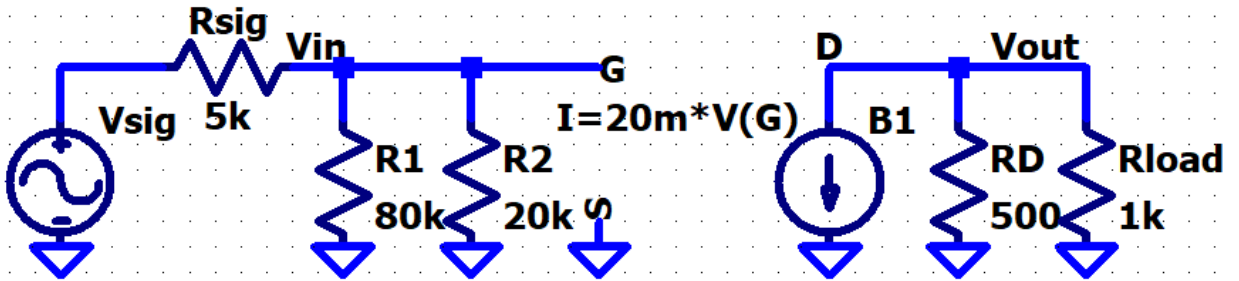
$$V_{RD} = R_D \cdot I_D$$

$$5\text{V} = R_D \cdot 10\text{mA}$$

$$R_D = 500\Omega$$

- c. (c) Determine the transconductance of the amplifier circuit (g_m) at the Q-point.
 $g_m = k(V_{GS} - V_{TH}) = 20\text{mA/V}^2 (2\text{V} - 1\text{V}) = 20\text{mA/V}$

- d. (d) Draw the AC small-signal equivalent circuit of the amplifier; include the signal source and load.



- e. (e) Calculate the open-circuit voltage amplification $AVOC$ (symbolic expression and numerical value). Also calculate the voltage amplification AV (symbolic expression and numerical value).

$$AVOC = V_{out}/V_{in} \mid_{RL=\infty}$$

$$AVOC = -g_m R_D = -10\text{mA} \cdot 500\Omega / V = -5$$

$$AV = V_{out}/V_{in}$$

$$AV = -g_m R_D / (g_m R_S + 1) = -20\text{m} \cdot 500 / (20\text{m} \cdot 5\text{k} + 1) = 10/101 = 0.099$$

- f. (f) Explain the following quantities:

- i. (i) Drain-gate capacitance C_{DG} and

The capacitance between the drain and gate of the MOSFET

- ii. (ii) the Miller capacitance C_{Miller} .

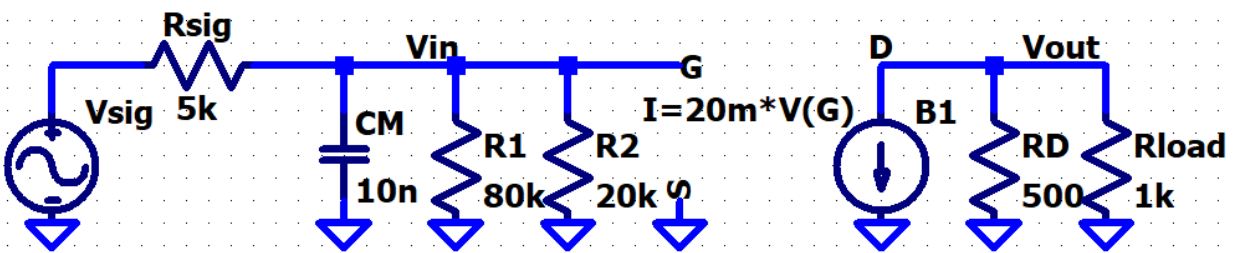
The capacitance in an inverting amp between the input and output terminals, the equivalent input capacitance

- g. (g) The experimental analysis of AV as a function of frequency reveals that the amplifier has a high-frequency cutoff at frequency $f_{Cutoff} = 20\text{ MHz}$. It is determined that the high-frequency cutoff is due to the Miller capacitance. Redraw the AC small signal equivalent circuit and now include the Miller capacitance. Determine the RC time constant ($\tau = RC$) of the input side of the circuit (symbolic expression and numerical value).

$$f_{Cutoff} = 1/T = 1/RC$$

$$C_M = 1/(R \cdot f_{Cutoff})$$

$$C_M = 1/(80\text{k} \cdot 20\text{Meg}) = 625\text{ fF}$$



$$T = RC = 1/f_{Cutoff} = 50\text{ ns}$$

- h. (h) Calculate the Miller capacitance (numerical value). Calculate the drain-gate capacitance CDG (numerical value).

$$f_{\text{Cutoff}} = 1/T = 1/RC$$

$$C_M = 1/(R * f_{\text{Cutoff}})$$

$$C_M = 1/(80k * 20\text{Meg}) = 625 \text{ fF}$$

$$C_M = (A_V + 1) C_{DG}$$

$$C_{DG} = C_M / (A_V + 1)$$

$$C_{DG} = 625\text{fF} / (1.099) = 568 \text{ fF}$$

- i. (i) Is there a basic amplifier configuration that suffers less (or not at all) from the limitations of the Miller capacitance?

Common D works well as a pre amp because of it's low output impedance, creating a smaller resistance, shorter time constant, and higher f_{Cutoff}